## AMENDMENT TO THE CLAIMS

- 1. (original) A method of making a diamond tool comprising the steps of:
- a) providing a ceramic mold having an interface surface configured to inversely match a configuration intended for a working surface of the tool;
  - b) forming a thin nucleation enhancer layer on the interface surface; and
- c) growing a diamond layer on the nucleation enhancer layer using a CVD technique, such that the working surface directly contacts the nucleation enhancer layer and receives the intended configuration from the interface surface of the mold.
- 2. (original) The method of claim 1, wherein the ceramic mold is made substantially of a material selected from the group consisting of oxides, nitrides, and mixtures thereof.
- 3. (original) The method of claim 2, wherein the oxide material is a member selected from the group consisting of: SiO<sub>2</sub>, Al<sub>2</sub>O<sub>3</sub>, LiTaO<sub>3</sub>, LiNbO<sub>3</sub>, ZnO, glass, and mixtures thereof.
- 4. (original) The method of claim 3, wherein the oxide material is  $Al_2O_3$ .
- 5. (original) The method of claim 4, wherein the nitride material is a member selected from the group consisting of: Si<sub>3</sub>N<sub>4</sub>, AlN, BN, TiN, ZrN, and mixtures thereof.
- 6. (original) The method of claim 5, wherein the nitride material is Si<sub>3</sub>N<sub>4</sub>.

- 7. (original) The method of claim 1, wherein the nucleation enhancer layer has a thickness of less than about 0.1 micrometers.
- 8. (presently amended) The method of claim 1, wherein the nucleation enhancer <u>layer</u> is made substantially of a material selected from the group consisting of: metals, metal alloys, metallic compounds, carbides, carbide formers, and mixtures thereof.
- 9. (currently amended) The method of claim 8, wherein the nucleation enhancer <u>layer</u> is made substantially of a carbide former selected from the group consisting of: tungsten (W), tantalum (Ta), titanium (Ti), zirconium (Zr), chromium (Cr), silicon (Si), molybdenum (Mo) and mixture thereof.
- 10. (currently amended) The method of claim 8, wherein the nucleation enhancer <u>layer</u> is made substantially of a carbide selected from the group consisting of: tungsten carbide (WC), silicon carbide (SiC), titanium carbide (TiC), zirconium carbide (ZrC) and mixtures thereof.
- 11. (original) The method of claim 1, wherein the interface surface has a surface roughness (Ra) of less than about 1 micrometer and wherein the working surface produced receives a surface roughness (Ra) of less than about 1 micrometer.
- 12. (original) The method of claim 1, wherein the ceramic mold is a piezoelectric material.

- 13. (original) The method of claim 12, wherein the piezoelectric material is a member selected from the group consisting of: SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub>, AlN, GaAs, GaP, LiTaO<sub>3</sub>, LiNbO<sub>3</sub>, ZnO, Pb(Zr, Ti)O<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub> Nb<sub>2</sub>O<sub>5</sub>, BeO, L<sub>2</sub>B<sub>4</sub>O<sub>7</sub>, KnbO<sub>3</sub>, ZnS, ZnSe, CdS, and mixtures thereof.
- 14. (original) The method of claim 12, wherein the piezoelectric material is provided from a single crystal ingot.
- 15. (original) The method of claim 1, wherein the tool is a surface acoustic wave (SAW) filter.
- 16. (original) The method of claim 1, further comprising the step of:
  separating the ceramic mold and nucleation enhancer layer from the diamond layer to expose the working surface.
- 17. (original) The method of claim 16, wherein said interface surface has a concave configuration.
- 18. (original) The method of claim 16, wherein said interface surface has a convex configuration.
- 19. (original) The method of claim 16, wherein said interface surface configuration inversely corresponds to the shape of a die.

- 20. (original) The method of claim 19, wherein said die has a channel with a non-spherical shape.
- 21. (presently amended) The method of claim 19, wherein the dye die is a wire drawing die.
- 22. (presently amended) The method of claim 19, wherein the dye die is an extrusion die.
- 23. (original) The method of claim 16, wherein said interface surface configuration inversely corresponds to the shape of a chemical mechanical polishing (CMP) pad dresser.
- 24. (original) The method of claim 16, wherein said interface surface configuration inversely corresponds to the shape of a pipe.
- 25. (original) The method of claim 16, wherein said interface surface configuration inversely corresponds to the shape of a diaphragm.
- 26. (original) The method of claim 16, wherein said interface surface configuration inversely corresponds to the shape of a cutting element.
- 27. (original) The method of claim 26, wherein said cutting element contains chip breakers.

- 28. (original) The method of claim 16, wherein said interface surface configuration inversely corresponds to the shape of a SAW filter.
- 29. (original) The method of claim 16, wherein said interface surface configuration inversely corresponds to the shape of a nozzle.
- 30. (original) The method of claim 16, wherein step of separating is accomplished by chemically removing the mold from the diamond layer.
- 31. (original) The method of claim 16, further comprising the step of forming a layer of piezoelectric material on the working surface.
- 32. (original) The method of claim 31, wherein the tool is a SAW filter.
- 33. (original) The method of either claims 1 or 16, further comprising the step of attaching said diamond layer to a non-diamond material for incorporation into a tool.
- 34. (original) A method of making a diamond tool comprising the steps of:
- a) providing a mold having an interface surface configured to inversely match a configuration intended for a working surface of the tool, said mold being made of a material selected from the group consisting of SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub>, AlN, GaAs, GaP, LiTaO<sub>3</sub>, LiNbO<sub>3</sub>, ZnO, Pb(Zr, Ti)O<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub> Nb<sub>2</sub>O<sub>5</sub>, BeO, L<sub>2</sub>B<sub>4</sub>O<sub>7</sub>, KnbO<sub>3</sub>, ZnS, ZnSe, CdS, and mixtures thereof;

- b) forming a thin nucleation enhancer layer on the interface surface, said nucleation enhancer being made of a material selected from the group consisting of tungsten (W), tantalum (Ta), titanium (Ti), zirconium (Zr), chromium (Cr), silicon (Si), molybdenum (Mo), carbides thereof, and mixtures thereof;
- c) growing a diamond layer on the nucleation enhancer layer using a CVD technique, such that the working surface directly contacts the nucleation enhancer layer and receives the intended configuration from the interface surface of the mold; and
- d) chemically separating the ceramic mold and nucleation enhancer layer from the diamond layer to expose the working surface.
- 35. (presently amended) The method of claim 3534, wherein the nucleation enhancer layer has a thickness of less than about 0.1 micrometers.
- 36. (presently amended) The method of claim 3635, wherein the interface surface has a surface roughness (Ra) of less than about 1 micrometer and wherein the working surface produced receives a surface roughness (Ra) of less than about 1 micrometer.
- 37. (presently amended) The method of claim 3736, wherein the mold material is provided from a single crystal ingot.
- 38. (presently amended) The method of claim 3837, wherein the tool is a surface acoustic wave (SAW) filter.

- 39. (presently amended) The method of claim 3534, wherein said interface surface has a concave configuration.
- 40. (presently amended) The method of claim 3534, wherein said interface surface has a convex configuration.
- 41. (presently amended) The method of claim 3534, wherein said interface surface configuration inversely corresponds to the shape of a die.
- 42. (presently amended) The method of claim 4241, wherein the dye die is a wire drawing die.
- 43. (presently amended) The method of claim 4241, wherein the dye die is an extrusion die.
- 44. (presently amended) The method of claim 3534, wherein said drawing die has a channel with a non-spherical shape.
- 45. (presently amended) The method of claim 3534, wherein said interface surface configuration inversely corresponds to the shape of a chemical mechanical polishing (CMP) pad dresser.

- 46. (presently amended) The method of claim 3534, wherein said interface surface configuration inversely corresponds to the shape of a pipe.
- 47. (presently amended) The method of claim 3534, wherein said interface surface configuration inversely corresponds to the shape of a diaphragm.
- 48. (presently amended) The method of claim <u>3534</u>, wherein said interface surface configuration inversely corresponds to the shape of a cutting element.
- 49. (presently amended) The method of claim 4948, wherein said cutting element contains chip breakers.
- 50. (original) A method of making a diamond tool consisting of the steps of:
- a) providing a ceramic mold having an interface surface configured to inversely match a configuration intended for a working surface of the tool;
  - b) forming a thin nucleation enhancer layer on the interface surface;
- c) growing a diamond layer on the nucleation enhancer layer using a CVD technique, such that the working surface directly contacts the nucleation enhancer layer and receives the intended configuration from the interface surface of the mold;
  - d) polishing an outside surface of the mold; and
  - e) forming a plurality of interdigital transducers (IDT) on the outside surface.

- 51. (presently amended) The method of claim 5150, wherein the nucleation enhancer is made substantially of a material selected from the group consisting of: metals, metal alloys, metallic compounds, carbides, carbide formers, and mixtures thereof.
- 52. (presently amended) The method of claim 5251, wherein the nucleation enhancer is a carbide former selected from the group consisting of: tungsten (W), tantalum (Ta), titanium (Ti), zirconium (Zr), chromium (Cr), silicon (Si), molybdenum (Mo) and mixture thereof.
- 53. (presently amended) The method of claim 5352, wherein the nucleation enhancer is a carbide selected from the group consisting of: tungsten carbide (WC), silicon carbide (SiC), titanium carbide (TiC), zirconium carbide (ZrC), and mixtures thereof.
- 54. (presently amended) The method of claim 5150, wherein the interface surface has a surface roughness (Ra) of less than about 1 micrometer and wherein the working surface produced receives a surface roughness (Ra) of less than about 1 micrometer.
- 55. (presently amended) The method of claim 5150, wherein the ceramic mold is a piezoelectric material.
- 56. (presently amended) The method of claim 5655, wherein the piezoelectric material is a member selected from the group consisting of: SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub>, AlN, GaAs, GaP, LiTaO<sub>3</sub>, LiNbO<sub>3</sub>, ZnO, Pb(Zr, Ti)O<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub> Nb<sub>2</sub>O<sub>5</sub>, BeO, L<sub>2</sub>B<sub>4</sub>O<sub>7</sub>, KnbO<sub>3</sub>, ZnS, ZnSe, CdS, and mixtures

thereof.

- 57. (presently amended) The method of claim 5655, wherein the piezoelectric material is provided from a single crystal ingot.
- 58. (presently amended) The method of claim 5150, wherein the tool is a surface acoustic wave (SAW) filter.
- 59. (original) A method of making a diamond tool consisting of the steps of:
- a) providing a mold of piezoelectric material having an interface surface with a roughness (Ra) less than about 1 nanometer, configured to inversely match a configuration intended for a working surface of the tool, said piezoelectric material being provide from a single crystal ingot selected from the group consisting of: SiO<sub>2</sub>, Si<sub>3</sub>N<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub>, AlN, GaAs, GaP, LiTaO<sub>3</sub>, LiNbO<sub>3</sub>, ZnO, Pb(Zr, Ti)O<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub> Nb<sub>2</sub>O<sub>5</sub>, BeO, L<sub>2</sub>B<sub>4</sub>O<sub>7</sub>, KnbO<sub>3</sub>, ZnS, ZnSe, CdS, and mixtures thereof;
- b) forming a thin nucleation enhancer layer on the interface surface, said nucleation enhancer being made of a material selected from the group consisting of: tungsten (W), tantalum (Ta), titanium (Ti), zirconium (Zr), chromium (Cr), silicon (Si), molybdenum (Mo), carbides thereof, and mixtures thereof;
- c) growing a diamond layer on the nucleation enhancer layer using a CVD technique, such that the working surface directly contacts the nucleation enhancer layer and receives the intended configuration from the interface surface of the mold;

- d) polishing an outside surface of the mold; and
- e) forming a plurality of interdigital transducers (IDT) on the outside surface.
- 60. (original) A method of making a diamond tool comprising the steps of:
- a) providing a carbide mold having an interface surface configured to inversely match a configuration intended for a working surface of the tool; and
- b) growing a diamond layer on the interface surface using a CVD technique, such that the working surface directly contacts the interface surface and receives the intended configuration from the interface surface of the mold.
- 61. (presently amended) The method of claim 6160, further comprising the step of: separating the carbide mold from the diamond layer to expose the working surface.
- 62. (presently amended) The method of claim 6160, wherein the carbide is a member selected from the group consisting of: tungsten carbide (WC), silicon carbide (SiC), titanium carbide (TiC), zirconium carbide (ZrC) and mixtures thereof.
- 63. (presently amended) The method of claim 6160, wherein the interface surface has a surface roughness (Ra) of less than about 1 micrometer and wherein the working surface produced receives a surface roughness (Ra) of less than about 1 micrometer.
- 64. (presently amended) The method of claim 6160, wherein the carbide is piezoelectric.

- 65. (presently amended) The method of claim 6564, wherein the tool is a SAW filter.
- 66. (original) A method of making a diamond tool consisting of the steps of:
- a) providing a carbide mold having an interface surface configured to inversely match a configuration intended for a working surface of the tool;
- b) growing a diamond layer on the interface surface using a CVD technique, such that the working surface directly contacts the interface surface and receives the intended configuration from the interface surface of the mold;
  - c) polishing an outside surface of the mold; and
  - d) forming a plurality of interdigital transducers (IDT) on the outside surface.
- 67. (original) A method of making a diamond tool comprising the steps of:
- a) providing a nitride mold having an interface surface configured to inversely match a configuration intended for a working surface of the tool; and
- b) growing a diamond layer on the interface surface using a CVD technique, such that the working surface receives the intended configuration from the interface surface of the mold.
- 68. (presently amended) The method of claim 6867, further comprising the step of: separating the nitride mold from the diamond layer to expose the working surface.

- 69. (presently amended) The method of claim 6867, wherein the nitride material is a member selected from the group consisting of: Si<sub>3</sub>N<sub>4</sub>, AlN, BN, TiN, ZrN, and mixtures thereof.
- 70. (presently amended) The method of claim 6867, wherein the interface surface has a surface roughness (Ra) of less than about 1 micrometer and wherein the working surface produced receives a surface roughness (Ra) of less than about 1 micrometer.
- 71. (presently amended) The method of claim 6867, wherein the nitride layer is provide as a single crystal ingot.
- 72. (presently amended) The method of claim 6867, wherein the tool is a SAW filter.
- 73. (original) A method of making a diamond tool consisting of the steps of:
- a) providing a nitride mold having an interface surface configured to inversely match a configuration intended for a working surface of the tool;
- b) growing a diamond layer on the interface surface using a CVD technique, such that the working surface directly contacts the interface surface and receives the intended configuration from the interface surface of the mold;
  - c) polishing an outside surface of the mold; and
  - d) forming a plurality of interdigital transducers (IDT) on the outside surface.
- 74. (withdrawn) A surface acoustic wave filter comprising:

- a) a diamond layer;
- b) a thin nucleation enhancer layer disposed on the diamond layer; and
- c) a piezoelectric layer disposed on the nucleation enhancer layer.